

Fast recovery Rectifier Diodes (Silicon Epitaxial Planar)

RF □□ 3 series

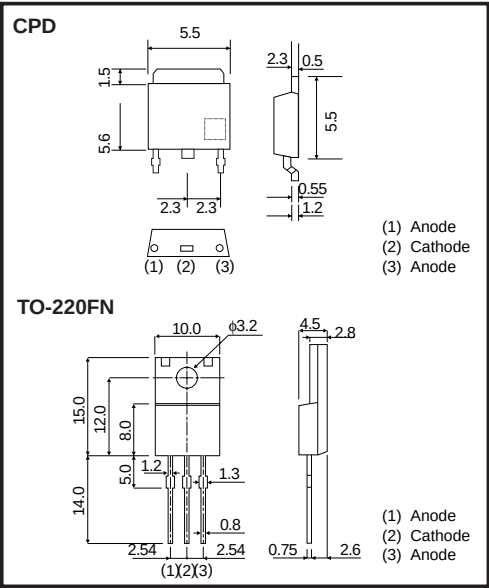
●Applications

High frequency rectification

●Features

- 1) Very fast recovery
- 2) Low V_F
- 3) Low switching loss
- 4) Standard package TO-220FN, CPD

●External dimensions (Unit : mm)



TO-220FN Center tap type cathode common, Dual elements



VR Io	Ultra low V_F type FRD		Fast recovery type FRD	
	200V		200V	
	Dual	Single	Dual	Single
6A	●	—	●	—
10A	●	—	●	—
15A	—	—	—	—
16A	●	—	—	—
20A	●	—	—	—
30A	—	—	—	—

CPD Center tap type cathode common, Dual elements



VR Io	Ultra low V_F type FRD		Fast recovery type FRD	
	200V		200V	
	Dual	Single	Dual	Single
3A	—	●	—	●
5A	—	●	—	●
6A	●	—	●	—
10A	—	—	—	—

Diodes

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits							Unit
		RF073M2S	RF103L2S	RF303B2S	RF503B2S	RF603B2D	RF603T2D	RF1003T2D	
Reverse voltage (repetitive peak)	V _{RM}	200	200	200	200	200	200	200	V
Reverse voltage (DC)	V _R	200	200	200	200	200	200	200	V
Average rectified forward current	I _O	0.7 ^{*1}	1.0 ^{*1}	3.0 ^{*1}	5.0 ^{*1}	6.0 ^{*1}	6.0 ^{*1}	10.0 ^{*1}	A
Forward peak surge current (60Hz · 1cyc.)	I _{FSM}	15	20	60	60	60	80	80	A
Junction temperature	T _j	150	150	150	150	150	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	-55 to +150	-55 to +150	-55 to +150	-55 to +150	-55 to +150	°C

* Mounting on glass epoxy board

●Electrical characteristics (Ta=25°C)

Part No.	IO	VR	VF			IR		trr		Configure	Package
			Max.	Typ.	IF	Max.	Typ.	Max.	Typ.		
RF073M2S	0.7A	200V	0.890V	0.830V	0.7A	10μA	1.2μA	20ns	9ns	Single	PMDU
RF103L2S	1A	200V	0.920V	0.860V	1A	10μA	1.2μA	20ns	9ns	Single	PMDS
RF303B2S	3A	200V	0.980V	0.920V	3A	20μA	2.0μA	20ns	11ns	Single	CPD(D-pack)
RF503B2S	5A	200V	0.980V	0.920V	5A	40μA	4.0μA	25ns	12ns	Single	CPD(D-pack)
RF603B2D	6A	200V	0.980V	0.920V	3A	20μA	2.0μA	20ns	11ns	Cathode common	CPD(D-pack)
RF603T2D	6A	200V	0.980V	0.920V	3A	20μA	2.0μA	20ns	11ns	Cathode common	TO-220FN
RF1003T2D	10A	200V	0.980V	0.920V	5A	40μA	4.0μA	25ns	12ns	Cathode common	TO-220FN